Correction to: Photoelectrochemical performance of dye and semiconductor sensitization on 1-D hollow hexagonal ZnO rods: A comparative study

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Unfortunately, in the original publication of the article, the Fig. 7 has an oversight. On Y-axis current density is “uA” rather than “mA”. The correct Figure is given below. The authors regret this error.

The online version of the original article can be found at <https://doi.org/10.1007/s10008-018-3995-y>

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Fig. 7 I–V measurement of Z₁, Z₂ and Z₃ thin films

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